

STB80NF10T4-VB Datasheet

N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
100	0.010 at $V_{GS} = 10$ V	100
	0.023 at $V_{GS} = 4.5$ V	85

FEATURES

- Trench Power MOSFET
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT

TO-263



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	100	A
		75 ^a	
Pulsed Drain Current	I_{DM}	300	
Avalanche Current	I_{AS}	75	
Single Pulse Avalanche Energy ^b	E_{AS}	280	mJ
Maximum Power Dissipation ^b	P_D	250 ^c	W
		3.75	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
		62.5	
Junction-to-Case	R_{thJC}	0.6	

Notes:

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^{\circ}\text{C}$			50	
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^{\circ}\text{C}$			250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = \geq 5\text{ V}, V_{GS} = 10\text{ V}$	120			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.010		Ω
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		0.023		
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$		0.020		
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$		0.030		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$	25			S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		6550		pF
Output Capacitance	C_{oss}			665		
Reverse Transfer Capacitance	C_{rss}			265		
Total Gate Charge ^c	Q_g	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 85\text{ A}$		105	160	nC
Gate-Source Charge ^c	Q_{gs}			17		
Gate-Drain Charge ^c	Q_{gd}			23		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong 85\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		12	25	ns
Rise Time ^c	t_r			90	135	
Turn-Off DelayTime ^c	$t_{d(off)}$			55	85	
Fall Time ^c	t_f			130	195	
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^{\circ}\text{C}$ ^b						
Continuous Current	I_S				85	A
Pulsed Current	I_{SM}				240	
Forward Voltage ^a	V_{SD}	$I_F = 85\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 50\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		85	140	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			4.5	7	A
Reverse Recovery Charge	Q_{rr}			0.17	0.35	μC

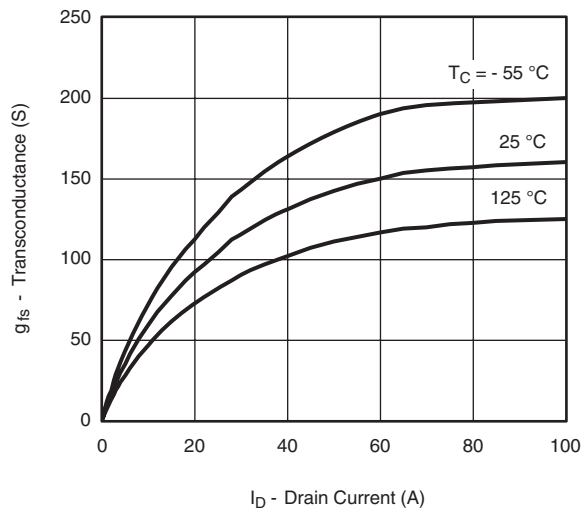
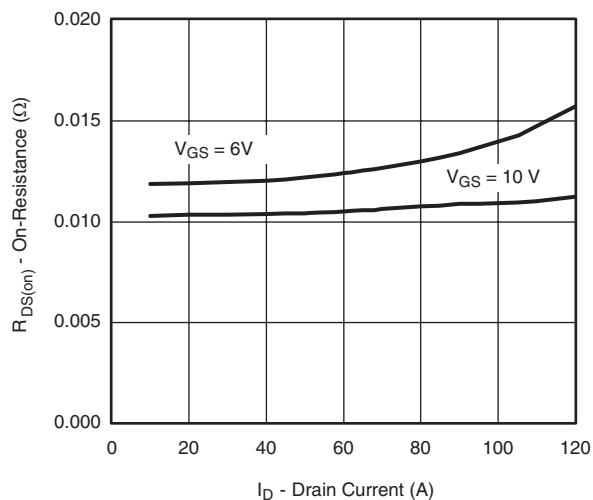
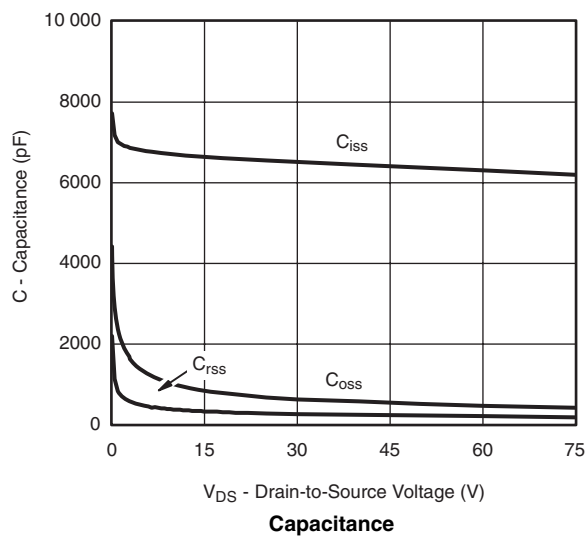
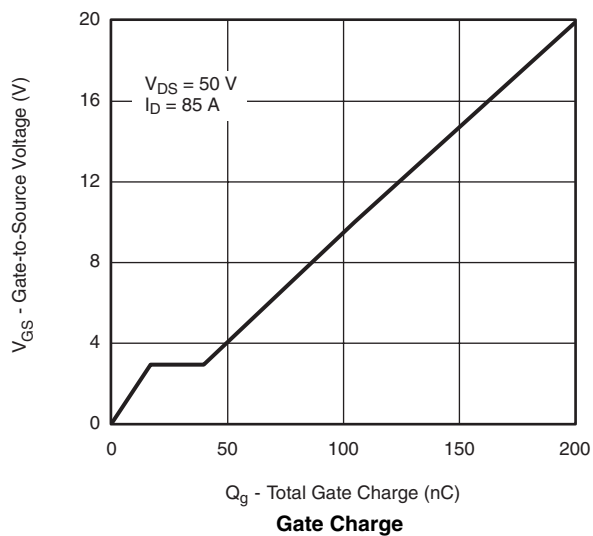
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

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TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

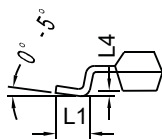
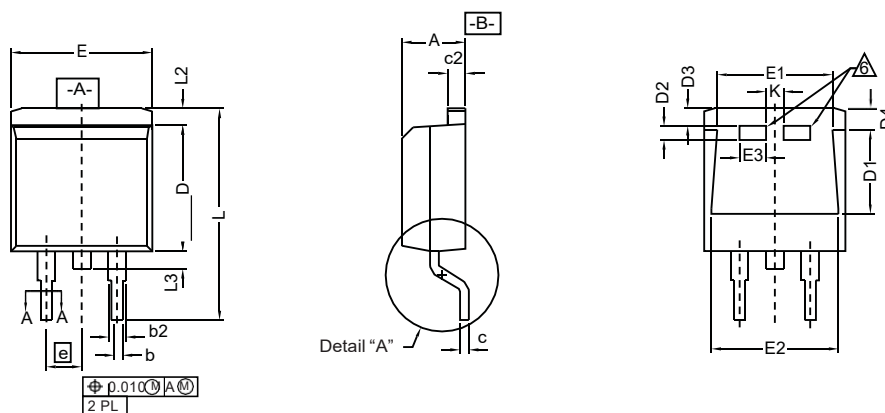
Avalanche Current vs. Time

 T_J - Drain-Source Breakdown vs. Junction-Temperature

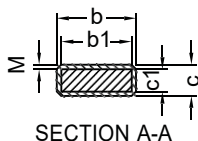
THERMAL RATINGS



TO-263 (D²PAK): 3-LEAD



DETAIL A (ROTATED 90°)



SECTION A-A

DIM.		INCHES		MILLIMETERS	
		MIN.	MAX.	MIN.	MAX.
A		0.160	0.190	4.064	4.826
b		0.020	0.039	0.508	0.990
b1		0.020	0.035	0.508	0.889
b2		0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2		0.045	0.055	1.143	1.397
D		0.340	0.380	8.636	9.652
D1		0.220	0.240	5.588	6.096
D2		0.038	0.042	0.965	1.067
D3		0.045	0.055	1.143	1.397
D4		0.044	0.052	1.118	1.321
E		0.380	0.410	9.652	10.414
E1		0.245	-	6.223	-
E2		0.355	0.375	9.017	9.525
E3		0.072	0.078	1.829	1.981
e		0.100 BSC		2.54 BSC	
K		0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
M		-	0.002	-	0.050

ECN: T13-0707-Rev. K, 30-Sep-13
DWG: 5843

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
-  This feature is for thick lead.

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